



ON Semiconductor®

SSR1N60BTM-WS / SSU1N60BTU-WS

N-Channel MOSFET

600 V, 0.9 A, 12 Ω

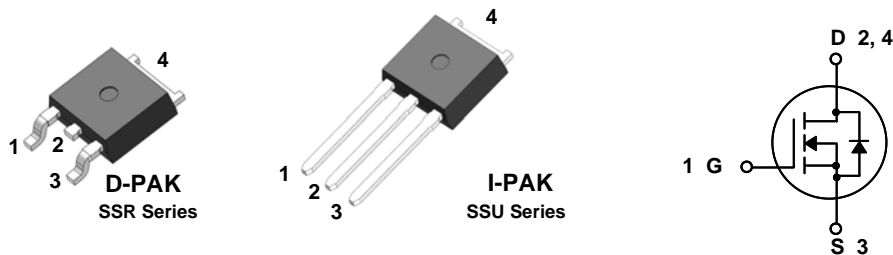
Features

- 0.9A, 600V, $R_{DS(on)} = 12\Omega @ V_{GS} = 10\text{ V}$
- Low gate charge (typical 5.9 nC)
- Low C_{rss} (typical 3.6 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Description

These N-Channel enhancement mode power field effect transistors are produced using ON Semiconductor's proprietary, planar, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	SSR1N60BTM-WS / SSU1N60BTU-WS	Unit
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	0.9	A
		0.57	
I_{DM}	Drain Current - Pulsed (Note 1)	3.0	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	50	mJ
I_{AR}	Avalanche Current (Note 1)	0.9	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	2.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	2.5	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	28	W
	- Derate above 25°C	0.22	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	-	4.53	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	-	50	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	110	$^\circ\text{C}/\text{W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	600	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	-	0.65	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	-	-	10	μA
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	-	-	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	-	-	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	-	-	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 0.45\text{ A}$	-	9.7	12	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 0.45\text{ A}$ (Note4)	-	0.92	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	-	165	215	pF
C_{oss}	Output Capacitance		-	18	25	pF
C_{rss}	Reverse Transfer Capacitance		-	3.6	4.7	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 1.0\text{ A},$ $R_G = 25\ \Omega$	-	14	40	ns
t_r	Turn-On Rise Time		-	45	100	ns
$t_{d(off)}$	Turn-Off Delay Time		-	25	60	ns
t_f	Turn-Off Fall Time		(Note 4,5)	-	35	80
Q_g	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 1.0\text{ A},$ $V_{GS} = 10\text{ V}$	-	5.9	7.7	nC
Q_{gs}	Gate-Source Charge		-	1.0	-	nC
Q_{gd}	Gate-Drain Charge		(Note 4,5)	-	2.7	-

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	0.9	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	3.0	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.9\text{ A}$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 1.0\text{ A},$	-	180	-	ns
Q_{rr}	Reverse Recovery Charge	$dI_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	-	0.47	-	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 115\text{ mH}, I_{AS} = 0.9\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$. Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 1.0\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$. Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

Figure 1. On-Region Characteristics

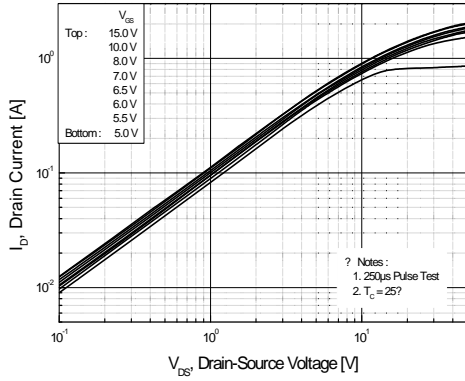


Figure 2. Transfer Characteristics

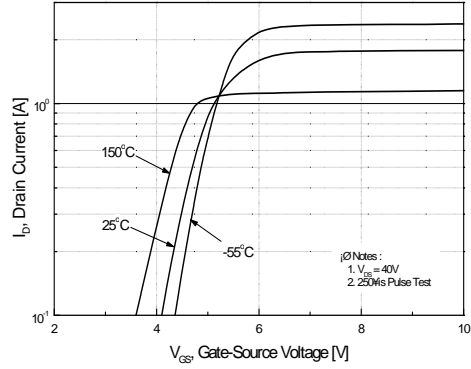


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

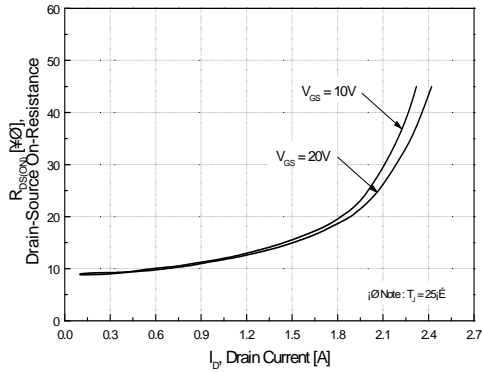


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

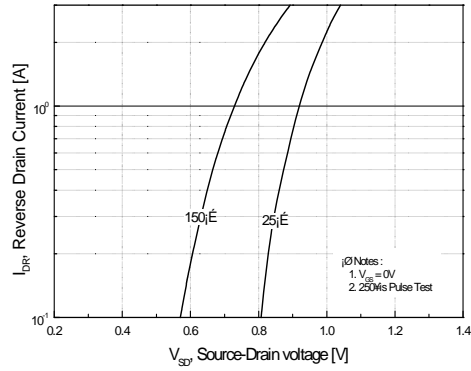


Figure 5. Capacitance Characteristics

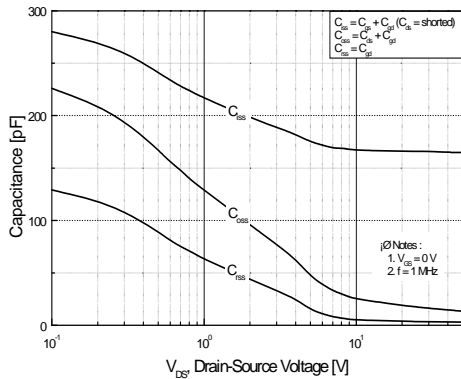
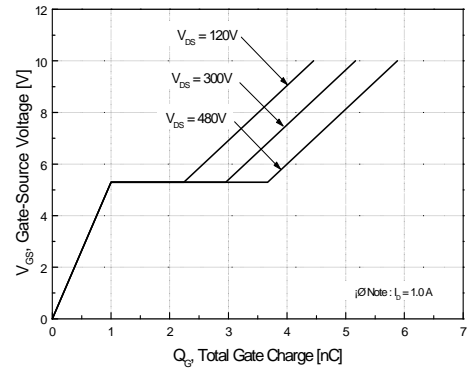


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

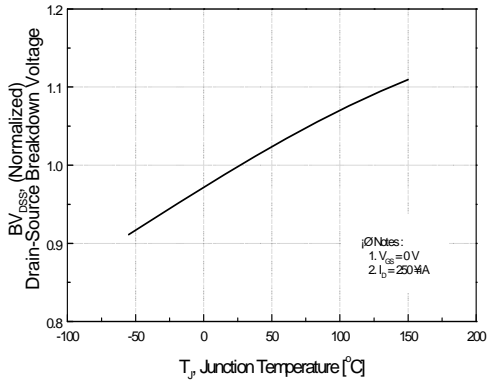


Figure 8. On-Resistance Variation vs. Temperature

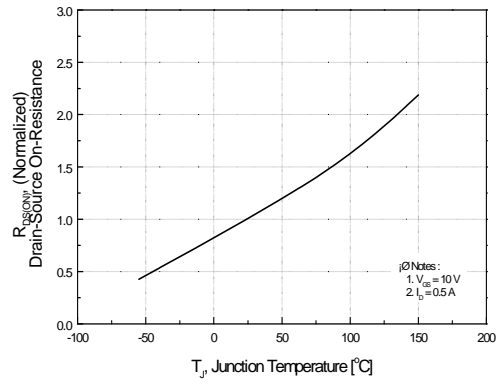


Figure 9. Maximum Safe Operating Area

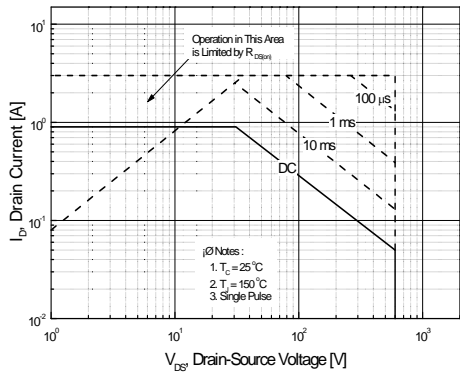


Figure 10. Maximum Safe Operating Area vs. Case Temperature

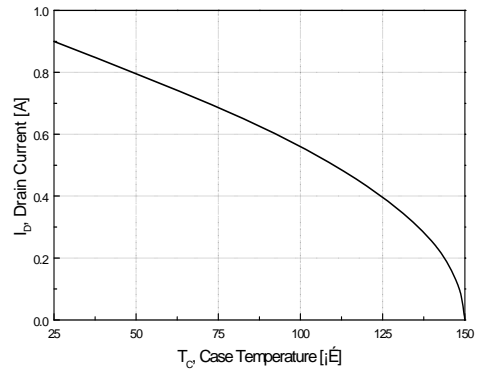


Figure 11. Transient Thermal Response Curve

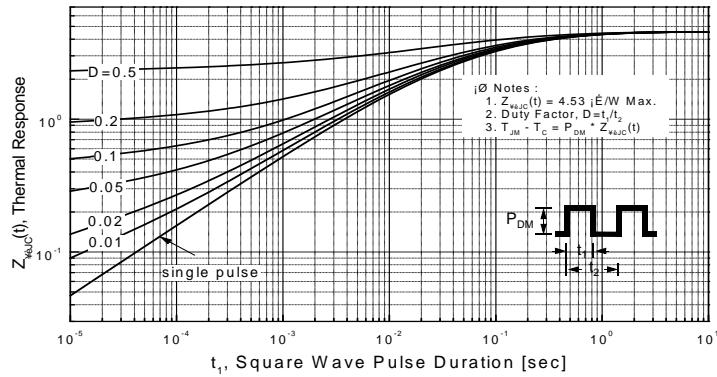


Figure 12. Gate Charge Test Circuit & Waveform

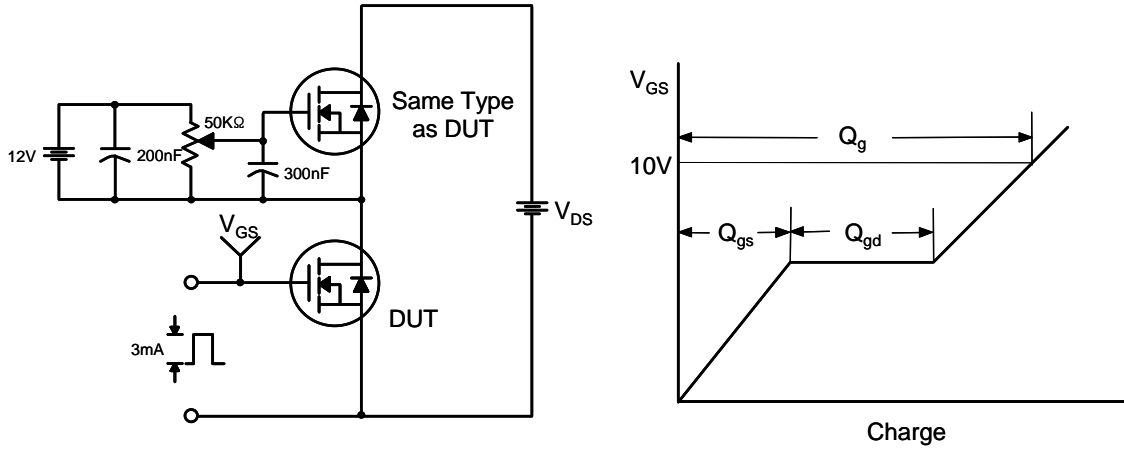


Figure 13. Resistive Switching Test Circuit & Waveforms

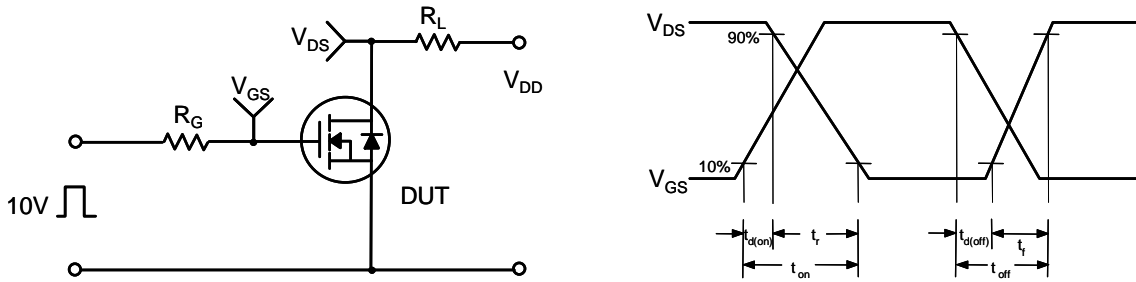


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

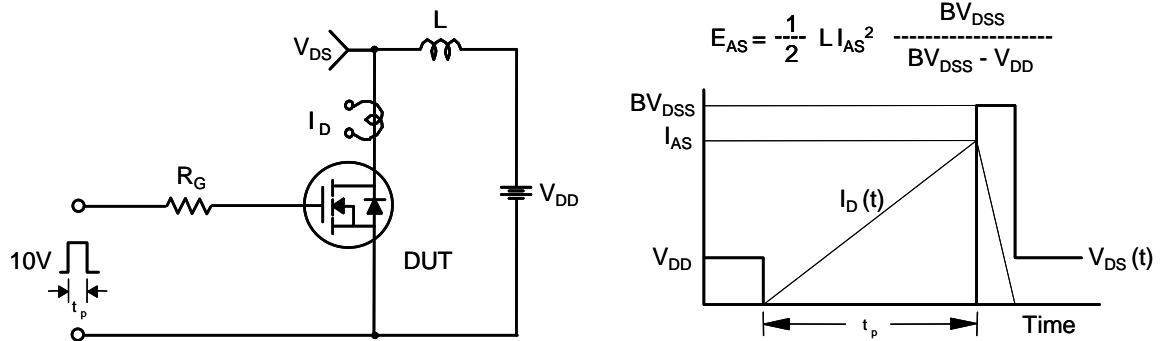
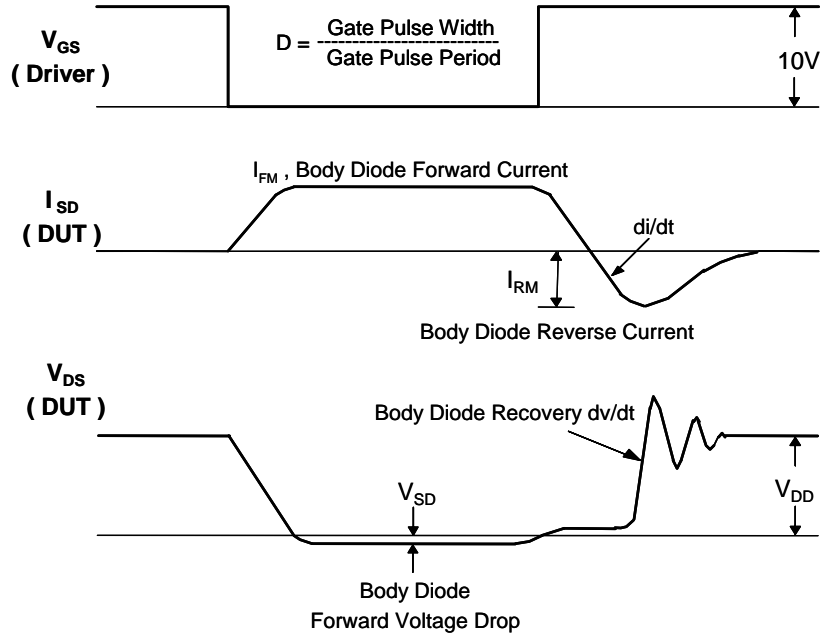
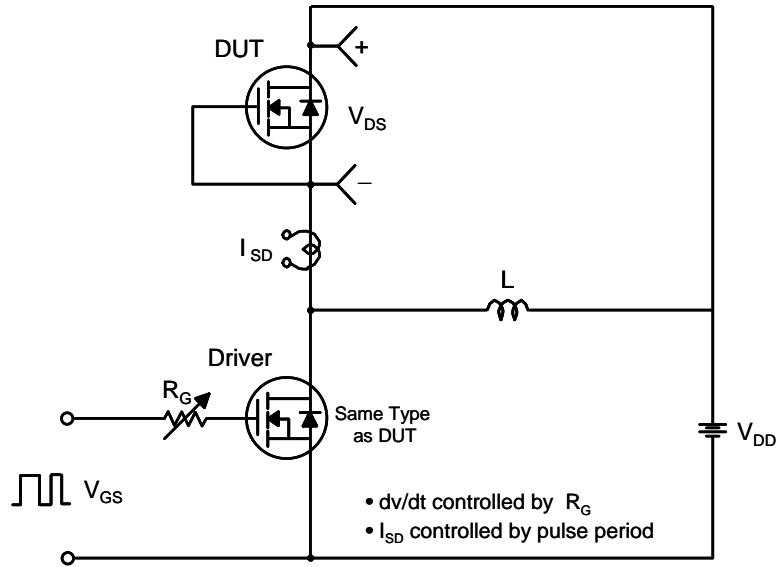
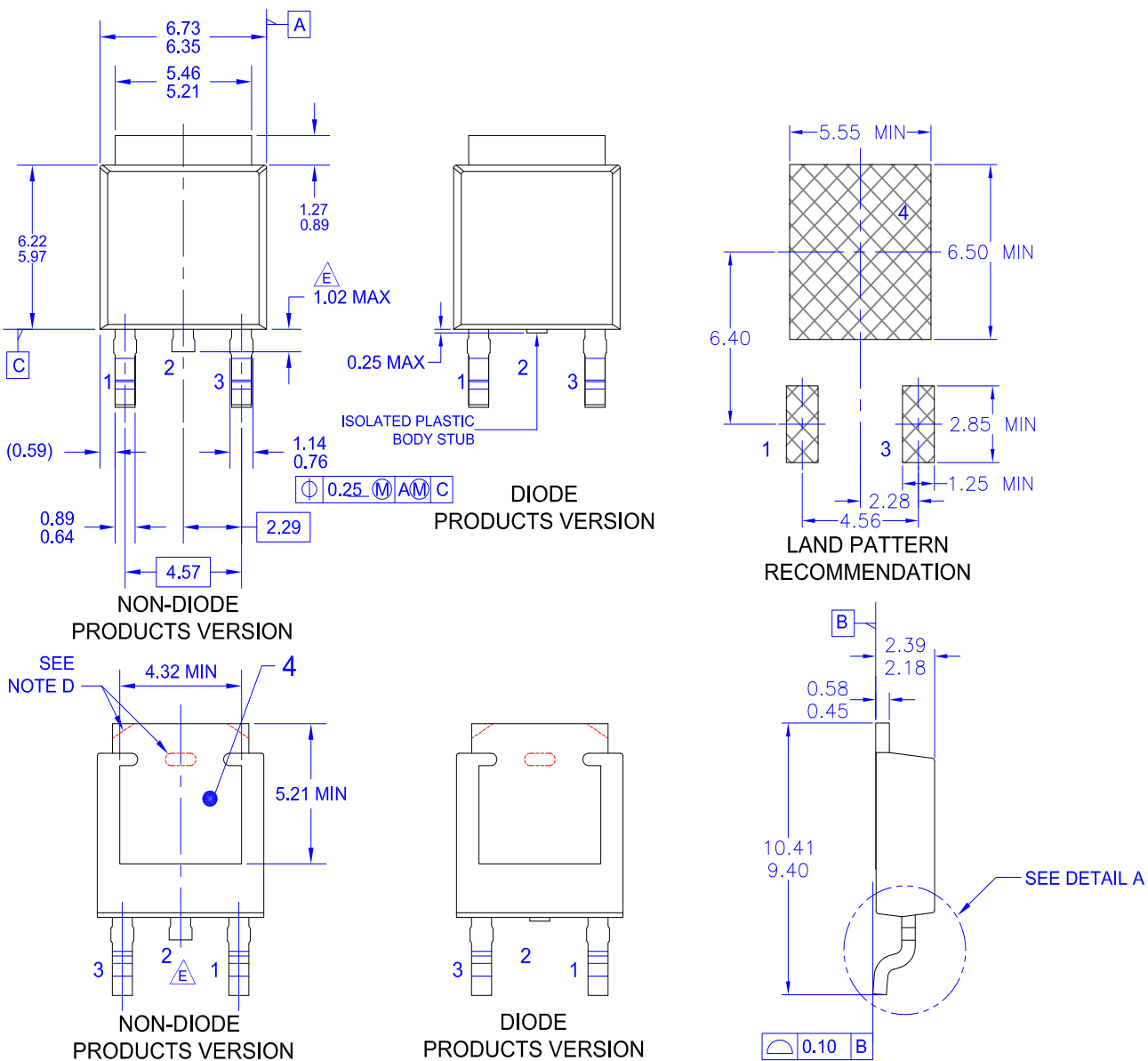


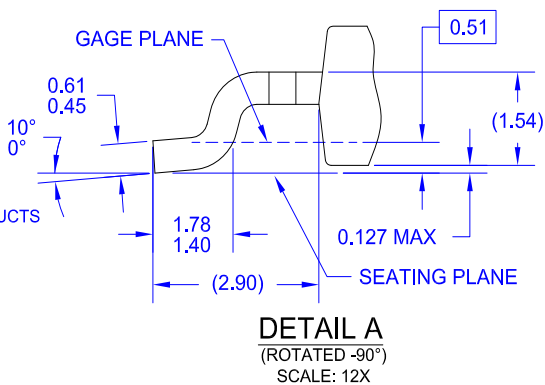
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

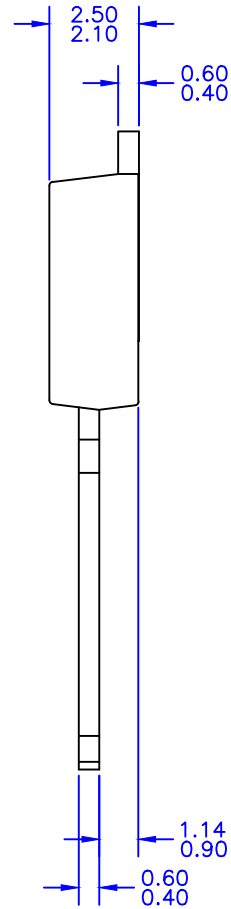
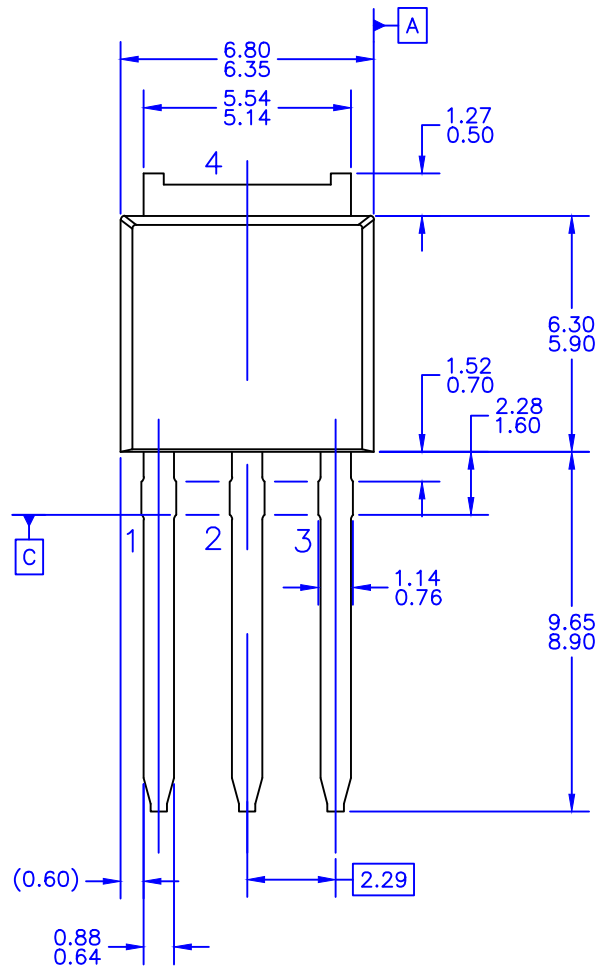




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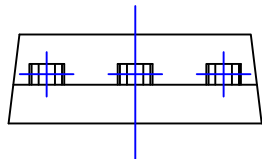
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